

ABSTRACT OF THE DISCLOSURE

A method of purging a semiconductor manufacturing apparatus comprises a step of etching a CVD-deposited film deposited in a chamber constituting a  
5 semiconductor manufacturing apparatus which has performed a process of forming a CVD film using a CVD process over a semiconductor wafer by using an etching gas containing at least a halogen gas, and a step of purging a cleaning gas remaining in the chamber by  
10 causing a gas containing hydrogen to flow into the chamber after the step of etching the CVD-deposited film by using the cleaning gas.